

NPN SILICON SWITCHING TRANSISTOR

Qualified per MIL-PRF-19500/423

Devices

2N5581

2N5582

Qualified Level

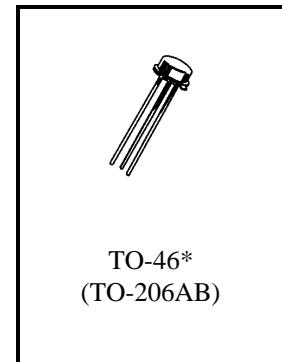
JAN
JANTX
JANTXV

MAXIMUM RATINGS

Ratings	Symbol	Value	Unit	
Collector-Emitter Voltage	V_{CEO}	50	Vdc	
Collector-Base Voltage	V_{CBO}	75	Vdc	
Emitter-Base Voltage	V_{EBO}	6.0	Vdc	
Collector Current	I_C	800	mAdc	
Total Power Dissipation	P_T	@ $T_A = 25^{\circ}\text{C}$ ⁽¹⁾	0.5	W
		@ $T_C = 25^{\circ}\text{C}$ ⁽²⁾	2.0	W
Operating & Storage Junction Temperature Range	T_{op}, T_{stg}	-55 to +200	$^{\circ}\text{C}$	

1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$ for $T_A > 25^{\circ}\text{C}$

2) Derate linearly 11.43 mW/ $^{\circ}\text{C}$ for $T_C > 25^{\circ}\text{C}$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$	$V_{(BR)CEO}$	50		Vdc
Collector-Base Cutoff Current $V_{CB} = 60 \text{ Vdc}$ $V_{CB} = 75 \text{ Vdc}$	I_{CBO}		10 10	ηAdc μAdc
Emitter-Base Cutoff Current $V_{EB} = 4.0\text{Vdc}$ $V_{EB} = 6.0\text{Vdc}$	I_{EBO}		10 10	ηAdc μAdc

2N5581, 2N5582 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS ⁽³⁾				
Forward-Current Transfer Ratio I _C = 0.1 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 500 mA _{dc} , V _{CE} = 10 V _{dc}	2N5581	h _{FE}	30 35 40 40 20	120
I _C = 0.1 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 500 mA _{dc} , V _{CE} = 10 V _{dc}	2N5582	h _{FE}	50 75 100 100 30	300
Collector-Emitter Saturation Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc} I _C = 500 mA _{dc} , I _B = 50 mA _{dc}	V _{CE(sat)}		0.3 1.0	V _{dc}
Base-Emitter Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc} I _C = 500 mA _{dc} , I _B = 50 mA _{dc}	V _{BE(sat)}	0.6	1.2 2.0	V _{dc}

DYNAMIC CHARACTERISTICS

Forward Current Transfer Ratio I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc}	2N5581 2N5582	h _{fe}	30 50	
Forward Current Transfer Ratio I _C = 50 mA _{dc} , V _{CE} = 20 V _{dc} , f = 100 MHz		h _{fe}	2.5	
Output Capacitance V _{CB} = 10 V _{dc} , I _E = 0, 100 kHz ≤ f ≤ 1.0 MHz		C _{obo}	8.0	pF
Input Capacitance V _{EB} = 0.5 V _{dc} , I _C = 0, 100 kHz ≤ f ≤ 1.0 MHz		C _{ibo}	25	pF

SWITCHING CHARACTERISTICS

Turn-On Time V _{CC} = 30 V _{dc} ; I _C = 150 mA _{dc} ; I _{B1} = 15 mA _{dc}	t _{on}		35	ns
Turn-Off Time V _{CC} = 30 V _{dc} ; I _C = 150 mA _{dc} ; I _{B1} = I _{B2} = 15 mA _{dc}	t _{off}		300	ns

(3) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.